

## General purpose PIN diode

### Features

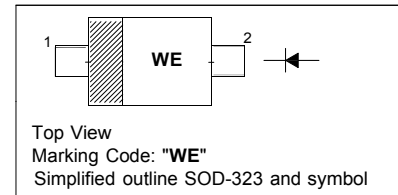
- Low forward resistance
- Low capacitance

### Applications

- General RF applications

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

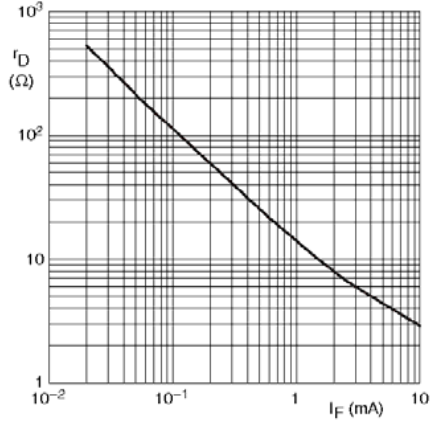


### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	50	V
Continuous Forward Current	$I_F$	50	mA
Total Power Dissipation ( $T_S = 90\text{ }^\circ\text{C}$ )	$P_{tot}$	500	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

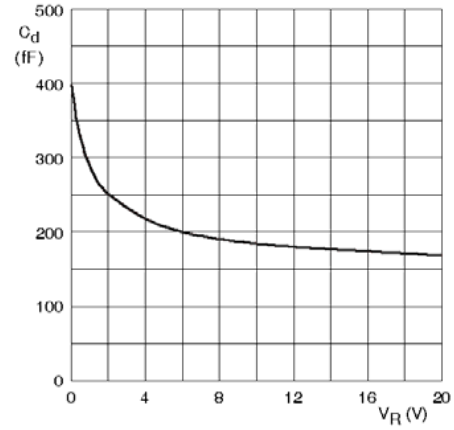
### Electrical Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 50\text{ mA}$	$V_F$	-	1.1	V
Reverse Current at $V_R = 50\text{ V}$	$I_R$	-	100	nA
Reverse Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_R$	50	-	V
Diode Capacitance at $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$ at $V_R = 5\text{ V}$ , $f = 1\text{ MHz}$	$C_d$	-	0.55 0.35	pF
Forward Resistance at $I_F = 0.5\text{ mA}$ , $f = 100\text{ MHz}$ at $I_F = 1\text{ mA}$ , $f = 100\text{ MHz}$ at $I_F = 10\text{ mA}$ , $f = 100\text{ MHz}$	$r_D$	-	40 25 5	$\Omega$



f = 100 MHz;  $T_j = 25^\circ\text{C}$ .

Forward resistance as a function of forward current; typical values.



f = 1 MHz;  $T_j = 25^\circ\text{C}$ .

Diode capacitance as a function of reverse voltage; typical values.